FAIRCHILD
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SSP4N60B/SSS4N60B

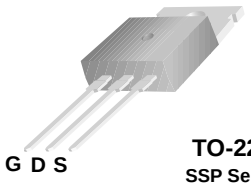
600V N-Channel MOSFET

General Description

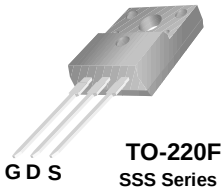
These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar, DMOS technology.
This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switch mode power supplies.

Features

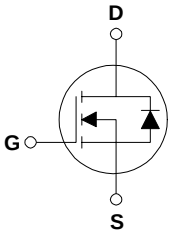
- 4.0A, 600V, $R_{DS(on)}$ = 2.5Ω @V_{GS} = 10 V
- Low gate charge (typical 22 nC)
- Low Crss (typical 14 pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability
- TO-220F package isolation = 4.0kV (Note 6)



TO-220
SSP Series



TO-220F
SSS Series



Absolute Maximum Ratings

T_C = 25°C unless otherwise noted

Symbol	Parameter		SSP4N60B	SSS4N60B	Units
V_{DSS}	Drain-Source Voltage		600		V
I_D	Drain Current - Continuous (T_C = 25°C)		4.0	4.0 *	A
	- Continuous (T_C = 100°C)		2.5	2.5 *	A
I_{DM}	Drain Current - Pulsed	(Note 1)	16	16 *	A
V_{GSS}	Gate-Source Voltage		± 30		V
E_{AS}	Single Pulsed Avalanche Energy	(Note 2)	240		mJ
I_{AR}	Avalanche Current	(Note 1)	4.0		A
E_{AR}	Repetitive Avalanche Energy	(Note 1)	10		mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	5.5		V/ns
P_D	Power Dissipation (T_C = 25°C)		100	33	W
	- Derate above 25°C		0.8	0.26	W/°C
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150		°C
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds		300		°C

* Drain current limited by maximum junction temperature

Thermal Characteristics

Symbol	Parameter	SSP4N60B	SSS4N60B	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case Max.	1.25	3.79	°C/W
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink Typ.	0.5	--	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient Max.	62.5	62.5	°C/W

Electrical Characteristics

T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0 V, I_D = 250 μA	600	--	--	V
ΔBV_{DSS} / ΔT_J	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, Referenced to 25°C	--	0.65	--	V/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 600 V, V_{GS} = 0 V	--	--	10	μA
		V_{DS} = 480 V, T_C = 125°C	--	--	100	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	V_{GS} = 30 V, V_{DS} = 0 V	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	V_{GS} = -30 V, V_{DS} = 0 V	--	--	-100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250 μA	2.0	--	4.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	V_{GS} = 10 V, I_D = 2.0 A	--	2.0	2.5	Ω
g_{FS}	Forward Transconductance	V_{DS} = 40 V, I_D = 2.0 A (Note 4)	--	4.7	--	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 25 V, V_{GS} = 0 V, f = 1.0 MHz	--	710	920	pF
C_{oss}	Output Capacitance		--	65	85	pF
C_{rss}	Reverse Transfer Capacitance		--	14	19	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 300 V, I_D = 4.0 A, R_G = 25 Ω (Note 4, 5)	--	20	50	ns
t_r	Turn-On Rise Time		--	55	120	ns
$t_{d(off)}$	Turn-Off Delay Time		--	70	150	ns
t_f	Turn-Off Fall Time		--	55	120	ns
Q_g	Total Gate Charge	V_{DS} = 480 V, I_D = 4.0 A, V_{GS} = 10 V (Note 4, 5)	--	22	29	nC
Q_{gs}	Gate-Source Charge		--	4.8	--	nC
Q_{gd}	Gate-Drain Charge		--	8.5	--	nC
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain-Source Diode Forward Current		--	--	4.0	A
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	16	A
V_{SD}	Drain-Source Diode Forward Voltage	V_{GS} = 0 V, I_S = 4.0 A	--	--	1.4	V
t_{rr}	Reverse Recovery Time	V_{GS} = 0 V, I_S = 4.0 A, dI_F / dt = 100 A/μs (Note 4)	--	330	--	ns
Q_{rr}	Reverse Recovery Charge		--	2.67	--	μC

Notes:
1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. L = 27.5mH, I_{AS} = 4.0A, V_{DD} = 50V, R_G = 25 Ω, Starting T_J = 25°C
3. $I_{SD} \leq$ 4.0A, di/dt $\leq$ 300A/μs, $V_{DD} \leq BV_{DSS}$, Starting T_J = 25°C
4. Pulse Test : Pulse width $\leq$ 300μs, Duty cycle $\leq$ 2%
5. Essentially independent of operating temperature
6. Only for back side in V_{iso} = 4.0kV and t = 0.3s

Typical Characteristics

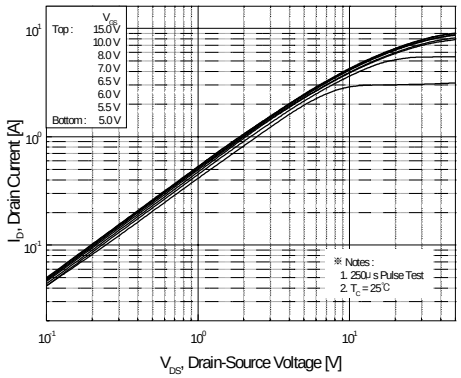


Figure 1. On-Region Characteristics

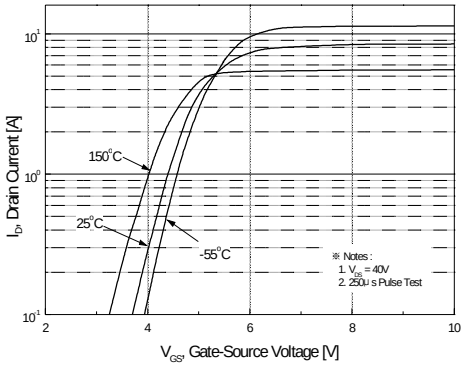


Figure 2. Transfer Characteristics

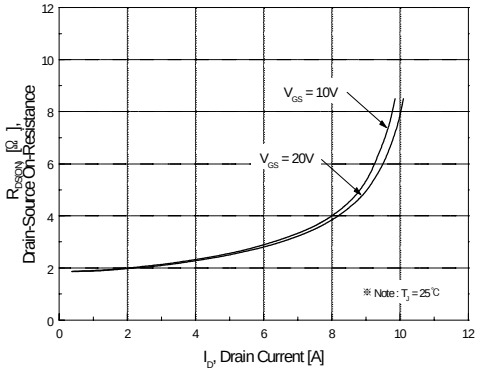


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

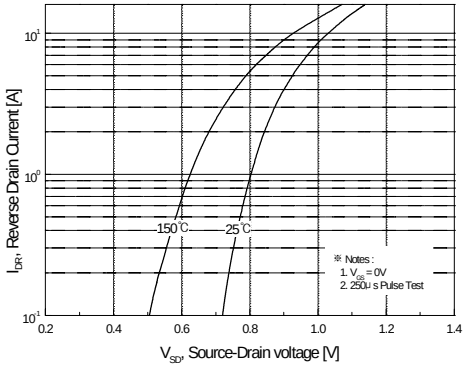


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

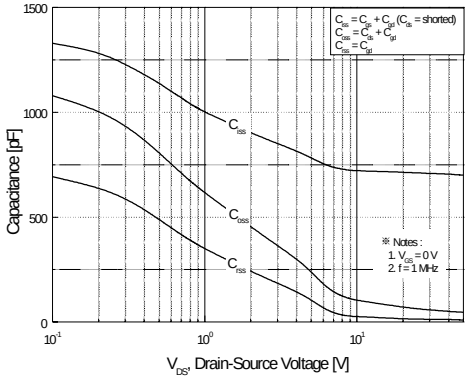


Figure 5. Capacitance Characteristics

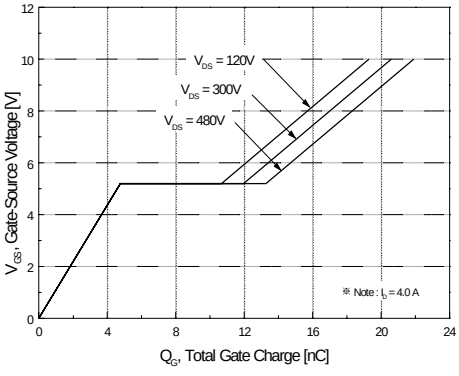


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

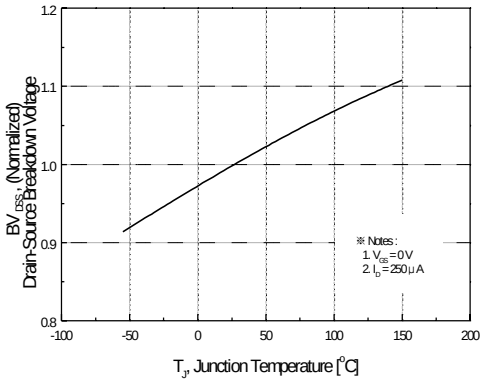


Figure 7. Breakdown Voltage Variation vs Temperature

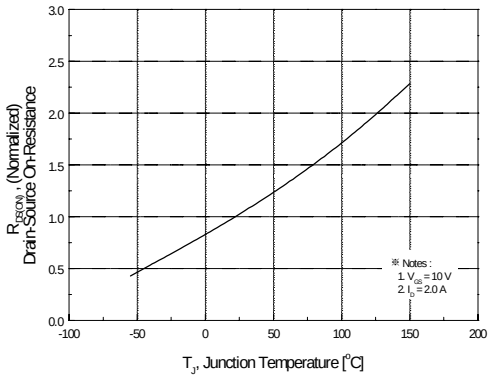


Figure 8. On-Resistance Variation

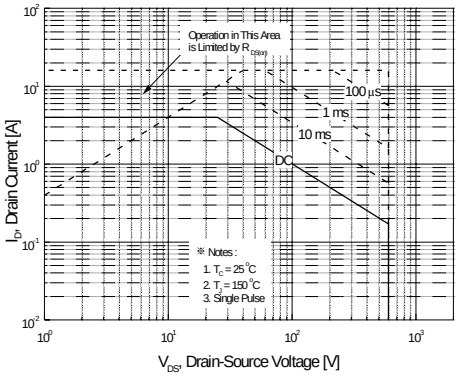


Figure 9-1. Maximum Safe Operating Area for SSP4N60B

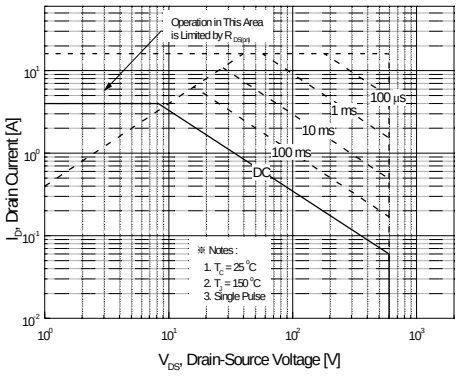


Figure 9-2. Maximum Safe Operating Area for SSS4N60B

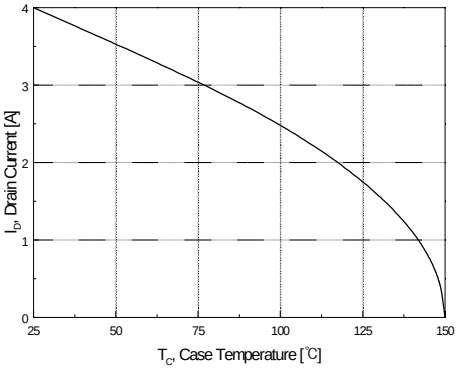


Figure 10. Maximum Drain Current vs Case Temperature

Typical Characteristics (Continued)

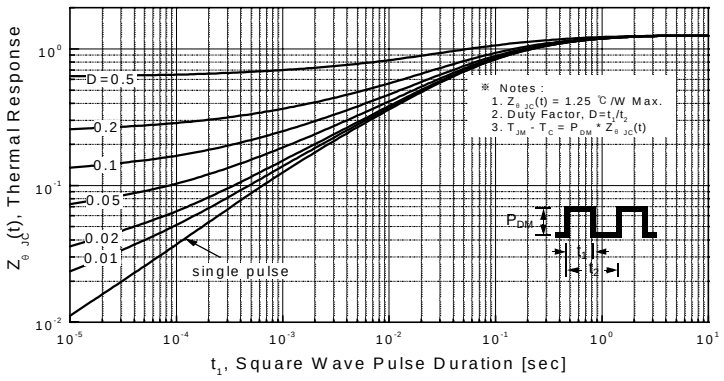


Figure 11-1. Transient Thermal Response Curve for SSP4N60B

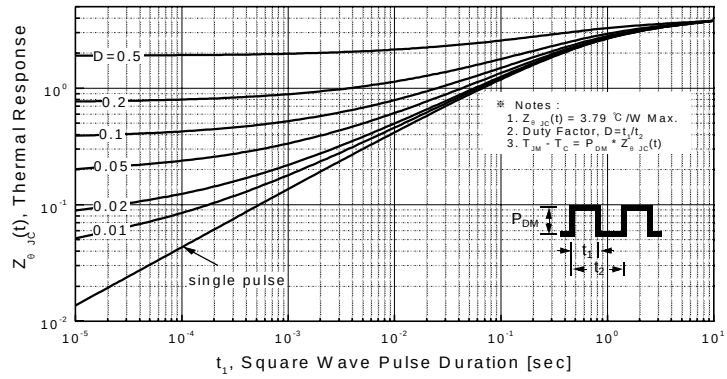
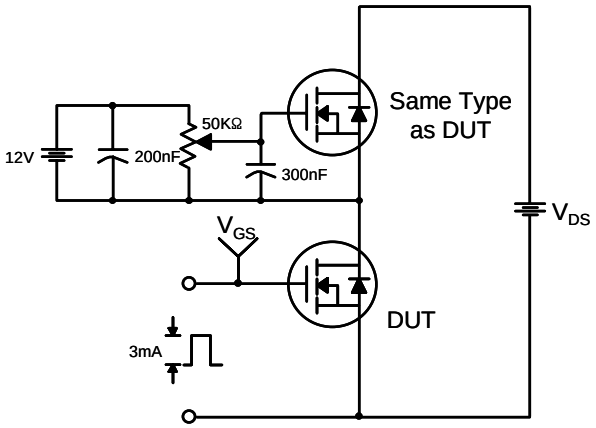
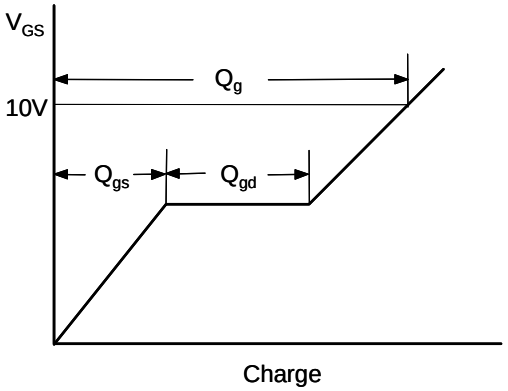


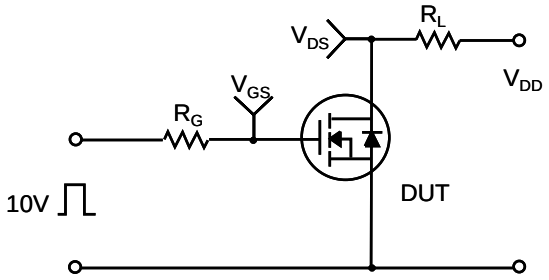
Figure 11-2. Transient Thermal Response Curve for SSS4N60B

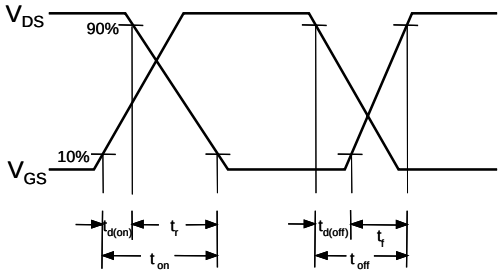
Gate Charge Test Circuit & Waveform



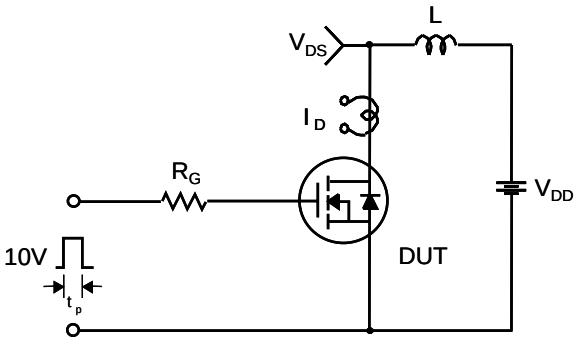


Resistive Switching Test Circuit & Waveforms

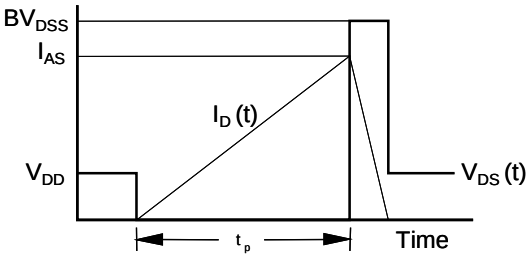




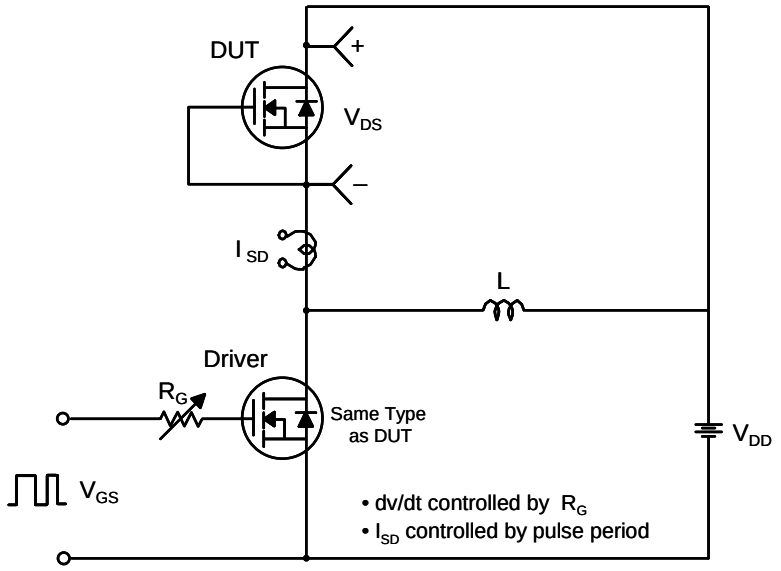
Unclamped Inductive Switching Test Circuit & Waveforms

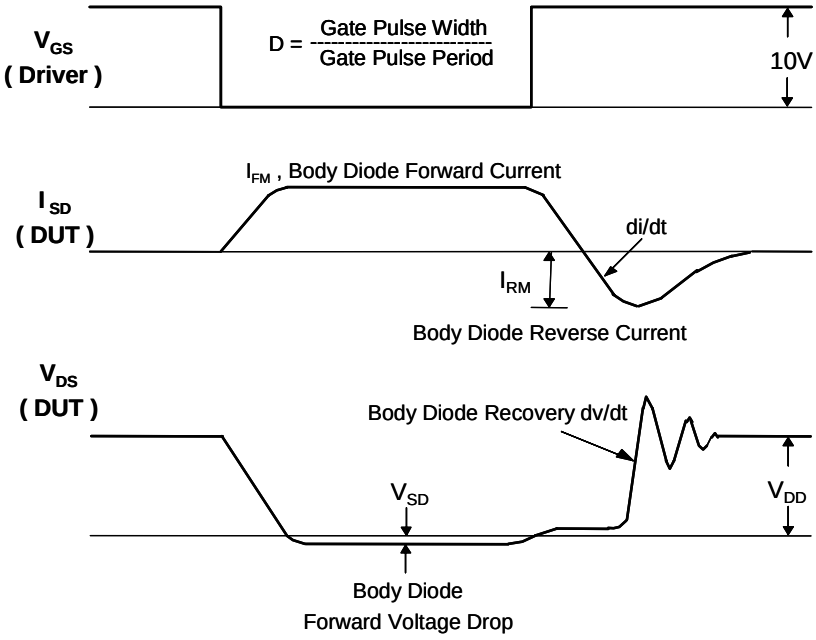


$$E_{AS} = \frac{1}{2} L I_{AS}^2 \frac{BV_{DSS}}{BV_{DSS} - V_{DD}}$$



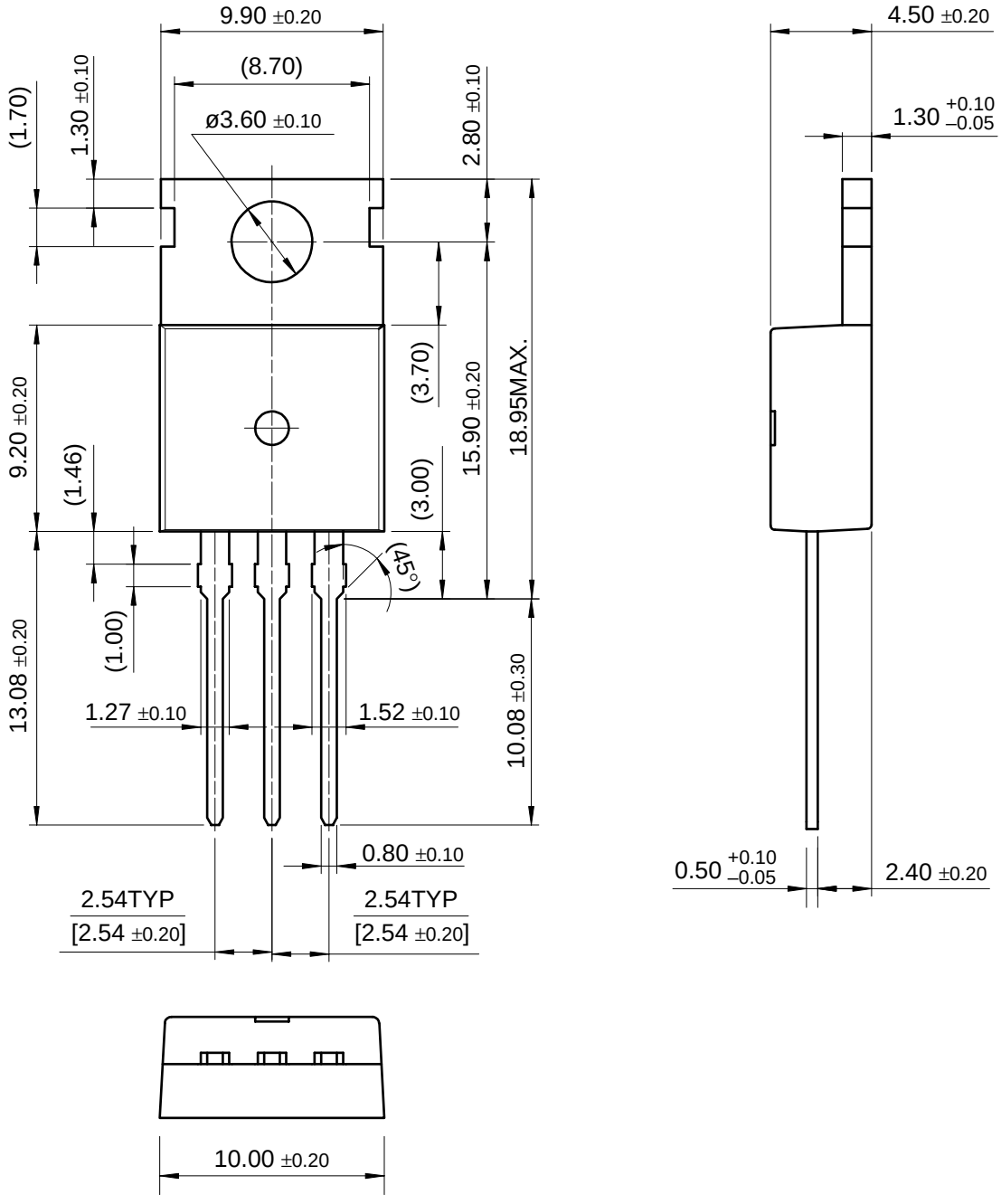
Peak Diode Recovery dv/dt Test Circuit & Waveforms





Package Dimensions

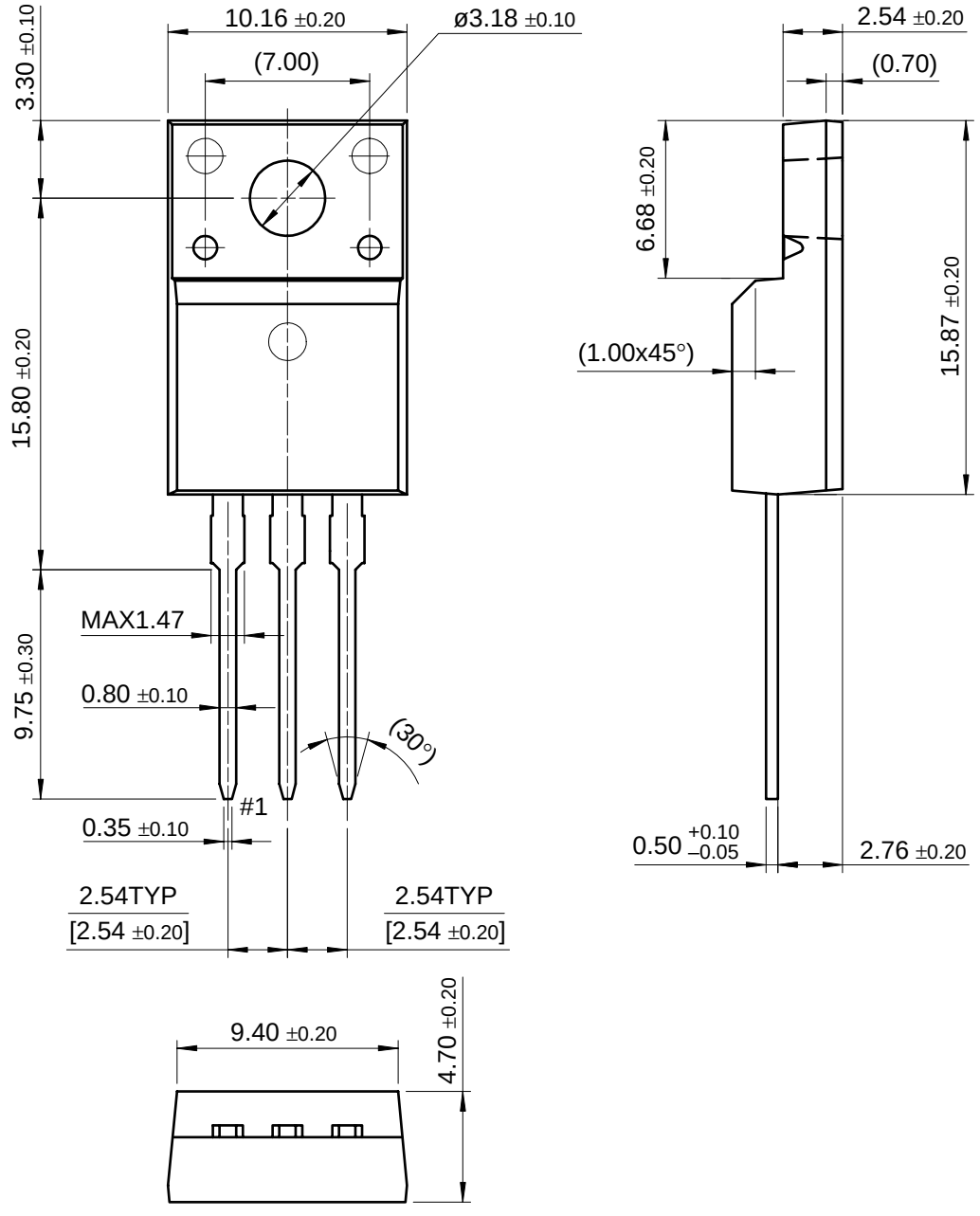
TO-220



Dimensions in Millimeters

Package Dimensions (Continued)

TO-220F



Dimensions in Millimeters

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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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